Switch-mode Power Rectifier

MURF1620CTG

These state-of-the-art devices are designed for use in switching power supplies, inverters and as free wheeling diodes.

Features

- Ultrafast 35 Nanosecond Recovery Times
- 150°C Operating Junction Temperature
- Epoxy Meets UL 94 V-0 @ 0.125 in
- High Temperature Glass Passivated Junction
- Low Leakage Specified @ 150°C Case Temperature
- Current Derating @ Both Case and Ambient Temperatures
- Electrically Isolated. No Isolation Hardware Required.
- ESD Rating:
 - ♦ Human Body Model = 3B (> 8 kV)
 - Machine Model = C (> 400 V)
- This is a Pb-Free Package*

Mechanical Characteristics:

- Case: Epoxy, Molded
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds



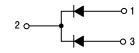
ON Semiconductor®

www.onsemi.com

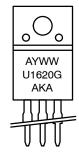
ULTRAFAST RECTIFIER16 AMPERES, 200 VOLTS



ISOLATED TO-220 FULLPAK™ CASE 221D



MARKING DIAGRAM



A = Assembly Location

Y = Year
WW = Work Week
U1620 = Device Code
G = Pb-Free Package
AKA = Diode Polarity

ORDERING INFORMATION

Device	Package	Shipping [†]
MURF1620CTG	TO-220 (Pb-Free)	50 Units / Rail

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MURF1620CTG

MAXIMUM RATINGS (Per Leg)

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	200	V
Average Rectified Forward Current Per Diode, (Rated V_R), T_C = 150°C Total Device	I _{F(AV)}	8 16	А
Peak Repetitive Forward Current (Rated V _R , Square Wave, 20 kHz), T _C = 150°C	I _{FM}	16	Α
Non-repetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I _{FSM}	100	Α
Operating Junction and Storage Temperature	T _J , T _{stg}	- 65 to +150	°C
RMS Isolation Voltage (t = 0.3 second, R.H. \leq 30%, T_A = 25°C) (Note 1)	V _{iso1}	4500	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS (Per Leg)

Characteristic	Symbol	Value	Unit
Maximum Thermal Resistance, Junction-to-Case	$R_{ heta JC}$	4.2	°C/W
Lead Temperature for Soldering Purposes: 1/8" from the Case for 5 seconds	TL	260	°C

ELECTRICAL CHARACTERISTICS (Per Leg)

Characteristic	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage (Note 2) ($i_F = 8.0 \text{ A}, T_C = 150^{\circ}\text{C}$) ($i_F = 8.0 \text{ A}, T_C = 25^{\circ}\text{C}$)	V _F	0.895 0.975	V
Maximum Instantaneous Reverse Current (Note 2) (Rated DC Voltage, $T_C = 150^{\circ}C$) (Rated DC Voltage, $T_C = 25^{\circ}C$)	i _R	250 5.0	μΑ
Maximum Reverse Recovery Time ($I_F = 1.0 \text{ A}$, $di/dt = 50 \text{ A/}\mu\text{s}$) ($I_F = 0.5 \text{ A}$, $I_R = 1.0 \text{ A}$, $I_{REC} = 0.25 \text{ A}$)	t _{rr}	35 25	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width = $300 \mu s$, Duty Cycle $\leq 2.0\%$.

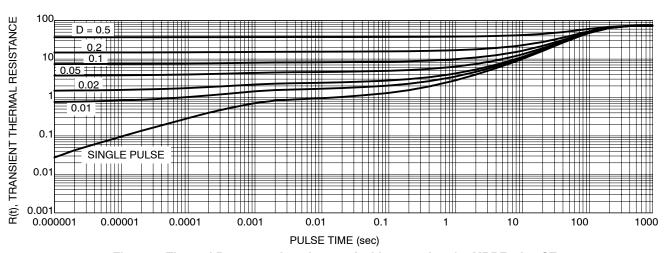


Figure 1. Thermal Response Junction-to-Ambient, per Leg for MBRF20L60CT

FULLPAK is a trademark of Semiconductor Components Industries, LLC (SCILLC) or its subsidiaries in the United States and/or other countries.

^{1.} Proper strike and creepage distance must be provided.

MECHANICAL CASE OUTLINE





SCALE 1:1

TO-220 FULLPAK CASE 221D-03 ISSUE K

DATE 27 FEB 2009

0

AYWW

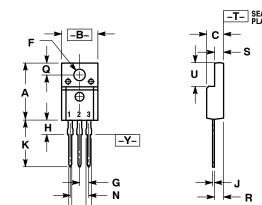
xxxxxxG

AKA



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH
- 221D-01 THRU 221D-02 OBSOLETE, NEW STANDARD 221D-03.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.617	0.635	15.67	16.12
В	0.392	0.419	9.96	10.63
С	0.177	0.193	4.50	4.90
D	0.024	0.039	0.60	1.00
F	0.116	0.129	2.95	3.28
G	0.100 BSC		2.54 BSC	
Н	0.118	0.135	3.00	3.43
J	0.018	0.025	0.45	0.63
K	0.503	0.541	12.78	13.73
L	0.048	0.058	1.23	1.47
N	0.200 BSC		5.08 BSC	
Q	0.122	0.138	3.10	3.50
R	0.099	0.117	2.51	2.96
S	0.092	0.113	2.34	2.87
U	0.239	0.271	6.06	6.88



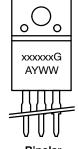
| ⊕ | 0.25 (0.010) M | B M | Y

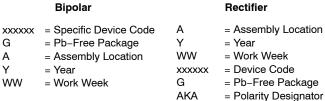
– **D** з PL

MARKING DIAGRAMS



STYLE 6: PIN 1. MT 1 2. MT 2 3. GATE STYLE 5: PIN 1. CATHODE 2. ANODE 3. GATE ANODE 3. CATHODE





DOCUMENT NUMBER:	98ASB42514B	Electronic versions are uncontrolled except when accessed directly from the Document Repositor Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	TO-220 FULLPAK		PAGE 1 OF 1	

Υ

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

ON Semiconductor and the are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor and see no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com

ON Semiconductor Website: www.onsemi.com

TECHNICAL SUPPORT North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative